



AZ[®] P4620 Photoresist Data Package

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AZ's Thick Film Photoresist Roadmap

Lift-off FT : 2-10 μm	TSV / Etch Implant, Plating FT : 3-15 μm	Copper/UBM Plating FT : 5-30 μm	Gold Plating FT : 10-30 μm	Solder / Metal Plating FT : >30 μm	MEMS / Ink Jet FT : >30 μm	DUV TFRH/Implant FT: 3 - 8 μm
Commercialized materials		AZ [®] P4620/ AZ [®] 4562				
AZ [®] nLOF Series	AZ [®] 2008HS					AZ [®] TX 1311 AZ [®] VS-01HJ
	AZ [®] 9260/10XT	AZ [®] PLP30/PLP40	AZ [®] 50XT			
AZ [®] N4000						
Advanced TF Products		AZ [®] 125nXT Series				AZ [®] TX VS-02HJ
AZ [®] 12XT Series				AZ [®] 40XT-11D		
AZ [®] 15nXT						
Materials under development		AZ [®] IPS-528				
AZ [®] 3DT-102						
		AZ [®] 125nXT-AD Series				

Red=Neg, Blue =Pos; nLOF, N4000, 15nXT, 12XT, 40XT = chemically amplified; 125nXT = photopolymer; 10XT, 9200, P4620, 2008HS, PLP, 50XT, 4500 = DNQ

AZ[®] Electronic Materials

Thick Photoresist Product Summary

Thick Film Product	Platform	λ	FT Range (um)	Maximum Single coat	Aspect Ratio	Application	Developer Compatibility
P4000 Series	DNQ	g-h	2 - 55	25	2:1	Solder, Cu, Au	400K / TMAH
4500 Series	DNQ	g-h	2 - 55	25	2:1	Solder, Cu, Au	400K / TMAH
9200 Series	DNQ	g-h-i	3 - 50	25	3:1	Solder, Cu, Au	400K / TMAH
10XT	DNQ	g-h-i	4 - 50	25	3:1	Solder, Cu, Au	400K / TMAH
50XT	DNQ	g-h	15 - 65	65	3:1	Solder, Cu, Etch	400K
PLP-30	DNQ	g-h	6 - 25	25	2:1	Au, Cu	303N
PLP-40	DNQ	g-h	20 - 30	30	2:1	Au, Cu	303N
12XT Series	CA	g-h-i	5 - 20	20	4:1	Si, Cu, Au, TSV	TMAH
40XT Series	CA	g-h-i	20 - 100	60	4:1	Etch, Solder, Cu	TMAH / 400K
125nXT Series	PP	g-h-i	20 - 120	120	6:1	Cu, Au, Solder	TMAH / 303N
15nXTA	CA	g-h-i	5 - 20	20	3:1	Cu, TSV Etch	TMAH
TX 1311	CA	DUV	3 - 5	5	15:1	Cu, NiFe, Si	TMAH

- Platform: **DNQ** = Novolak, **CA** = Chemically Amplified, **PP** = Photopolymer
- Wavelength: Red font indicates better performance.
- Developer Compatibility: **Bold font** indicates most compatible developer, resulting in shorter develop times and lower exposure energies.

AZ P4620 Process Conditions:

Optitrac Coat/ Bake

Coat: Static dispense on Silicon

Target Film Thickness: **15 μm**

Softbake: 110 C hotplate/ 180 sec. HP

Exposure: PLA-501F ghi line Aligner

Develop: AZ 400K 1:4, Immersion for 300 sec., 23 C

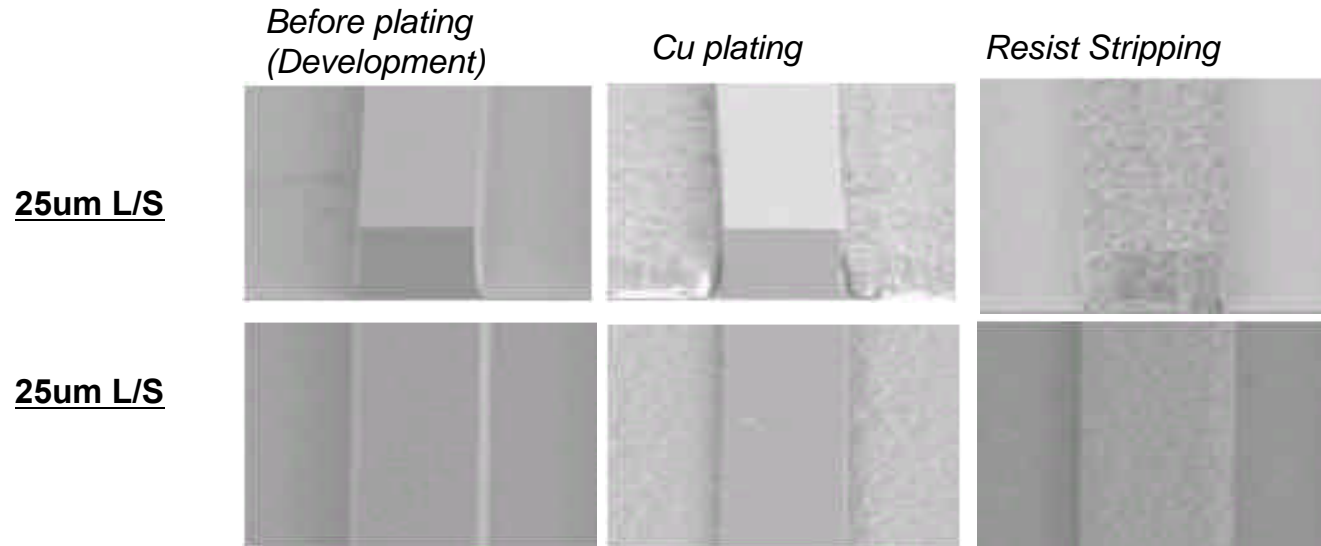
Plating liquid: **MICROFAB Cu200** (EEJA)

Plating height: 7.0um, Plating: 25 C / 30 min.

Analysis:

Amray SEM

AZ P4620 Copper plating



Plating process condition

Photoresist thickness: **15um**, Prebake: 110 C / 180 sec (Hotplate)

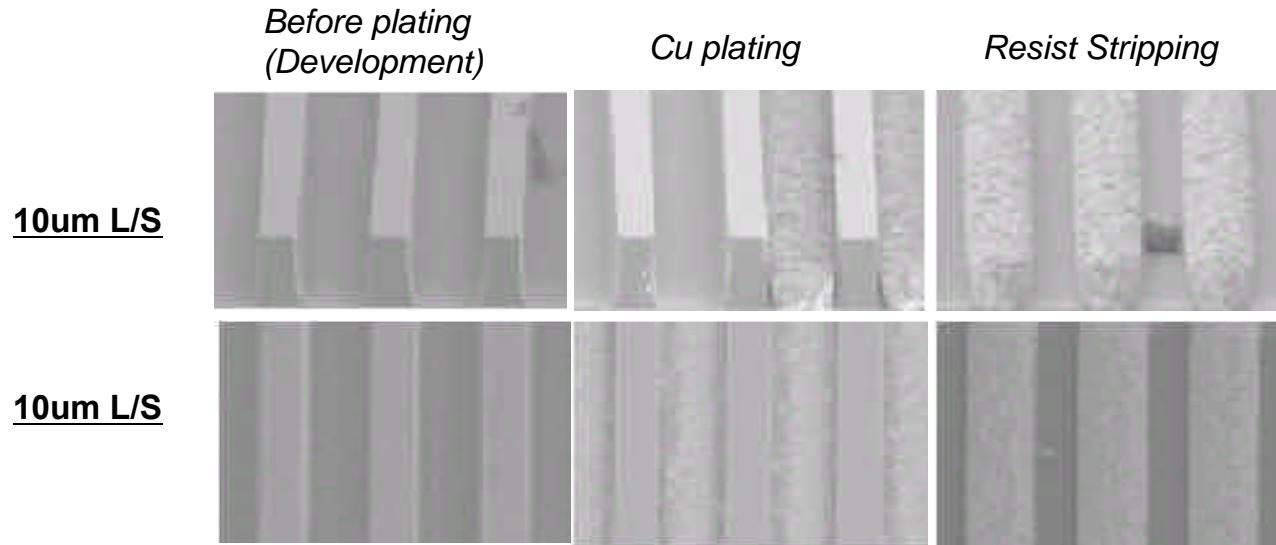
Exposure: PLA-501F (Soft contact, ghi-line aligner)

Development: AZ 400K 1:4, Immersion for 300 sec, 23 C

Plating liquid: **MICROFAB Cu200** (EEJA)

Plating height: 7.0um, Plating: 25 C / 30 min.

AZ P4620 Copper plating



Plating process condition

Photoresist thickness: **15um**, Prebake: 110C/180 sec. (Hotplate)

Exposure: PLA-501F (Soft contact, ghi-line aligner)

Development: AZ 400K 1:4, Immersion for 300 sec., 23 C

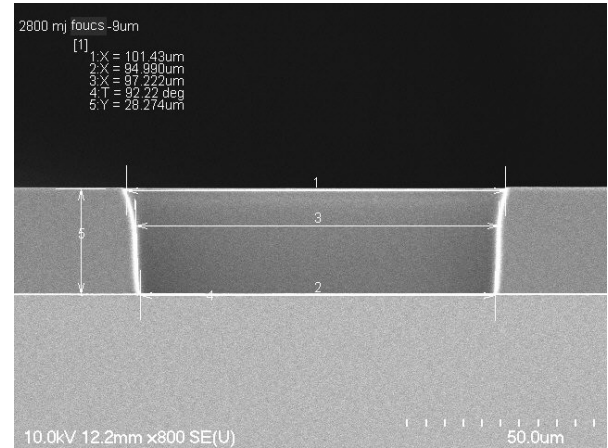
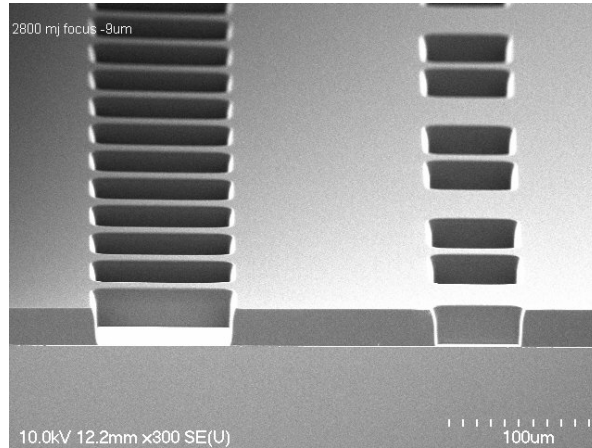
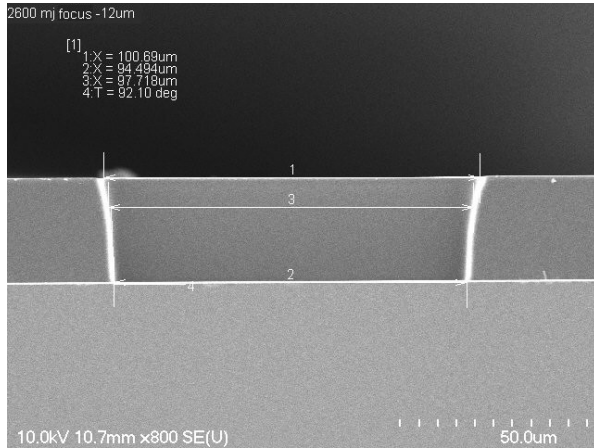
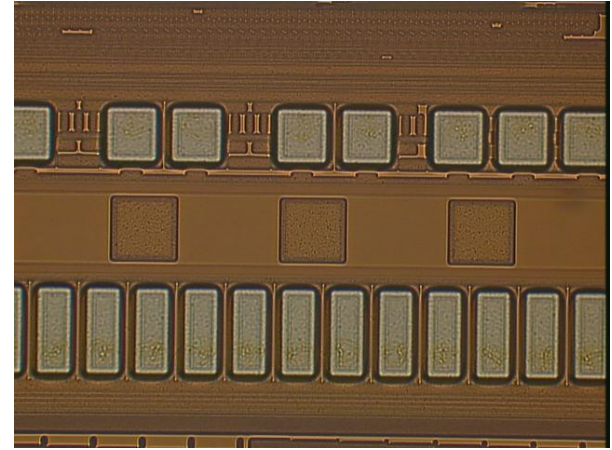
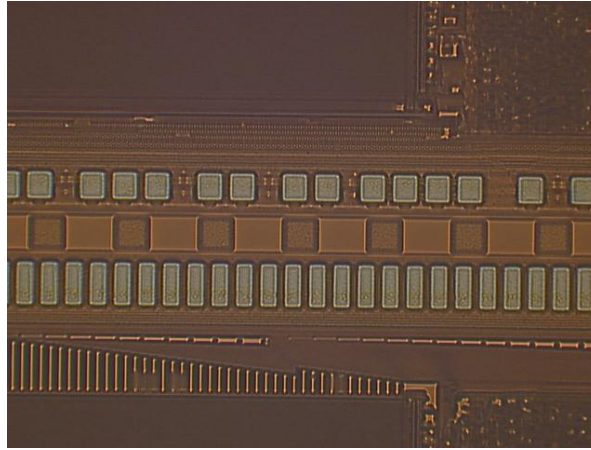
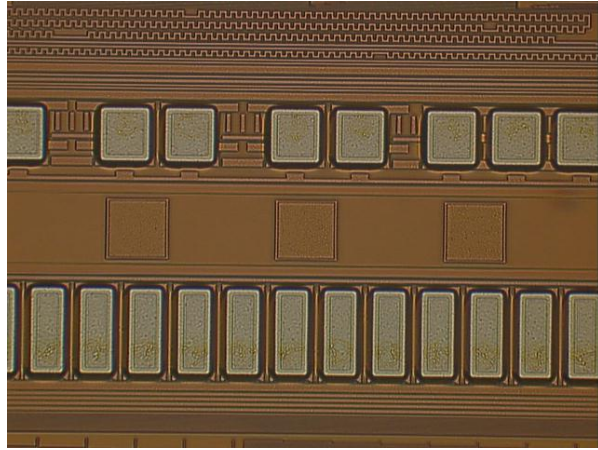
Plating liquid: **MICROFAB Cu200** (EEJA)

Plating height: 7.0um, Plating: 25 C / 30 min.

AZ[®] P4620 Gold Plating Process

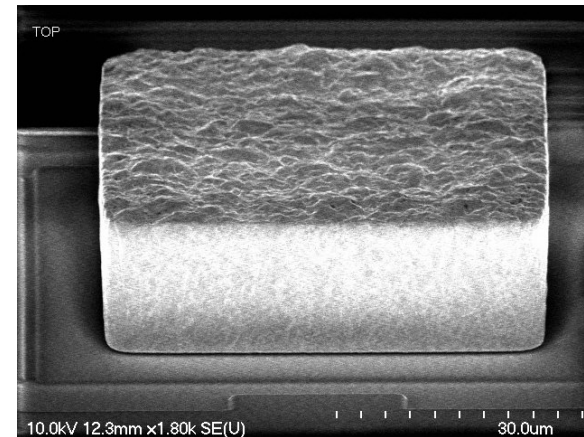
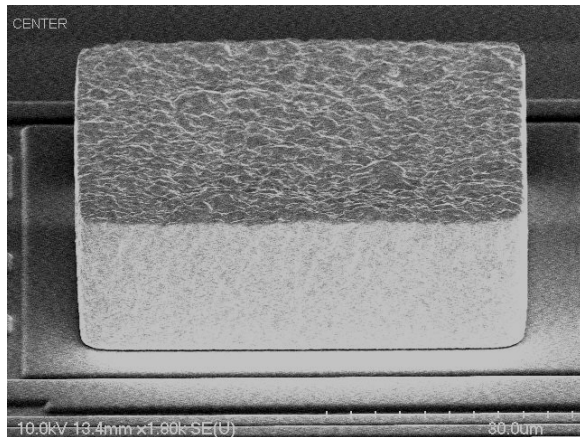
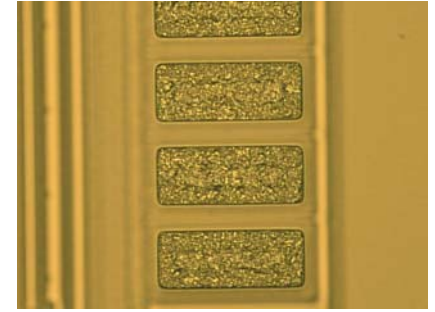
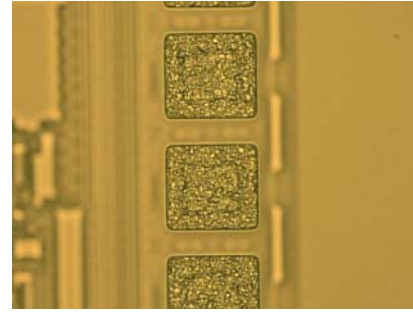
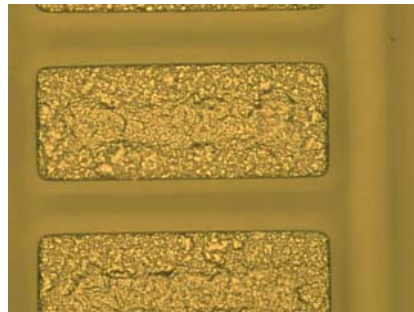
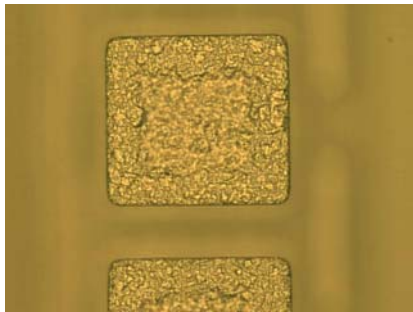
FT: 28um, Single Coat
Softbake: 1) 100°C / 500 sec. (Hotplate)
2) 90°C / 180 min. (Oven)
Rehydration time: 60 minutes
Exposure: UTS-SS-III (ghi-line)
Develop: AZ 400K 1:3, 21.5°C
Plating: Cyanide Gold Plating Solution

AZ[®] P4620 Gold Plating Process



AZ[®] P4620 Gold Plating Process

Photoresist Mask CD = 93.5 μ m; Au Bump CD = 96 μ m.



AZ P4620 Lithography performance

Process Conditions:

Optitrac Coat/ Bake

Coat: Static dispense on Silicon

Target Film Thickness: **12 μm**

Softbake: 110C hotplate/ 80 sec. full contact

Exposure: Ultratech 1500 gh line Stepper

Develop: AZ[®] 300 MIF, continuous spray for 200 sec. @ 23 C

Analysis:

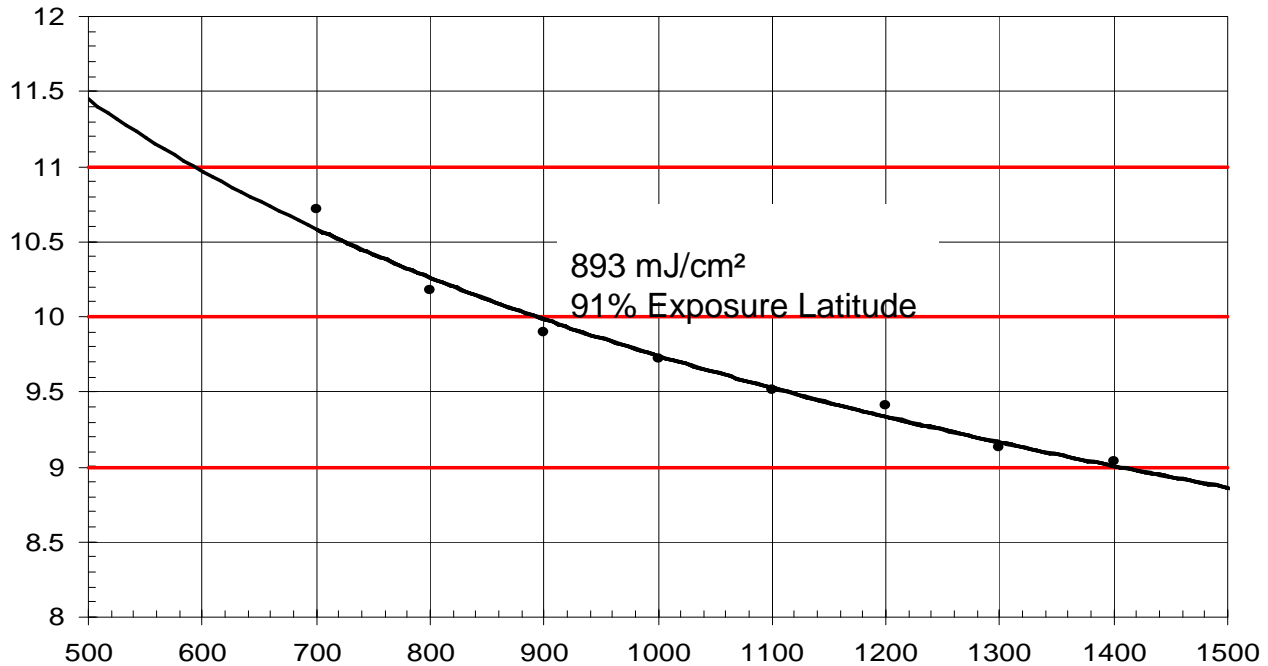
Amray SEM

AZ P4620 Lithography performance

Summary of Results:

	(mm)	DTP 10 mm (mJ/cm ²)	Exposure Latitude 10 mm (%)	DOF 10 mm (mm)	Linearity (mm)
Dense Lines	12	893	91	16	4.0
Contact Holes	12	927	91	>8	<10

AZ P4620 Lithography performance



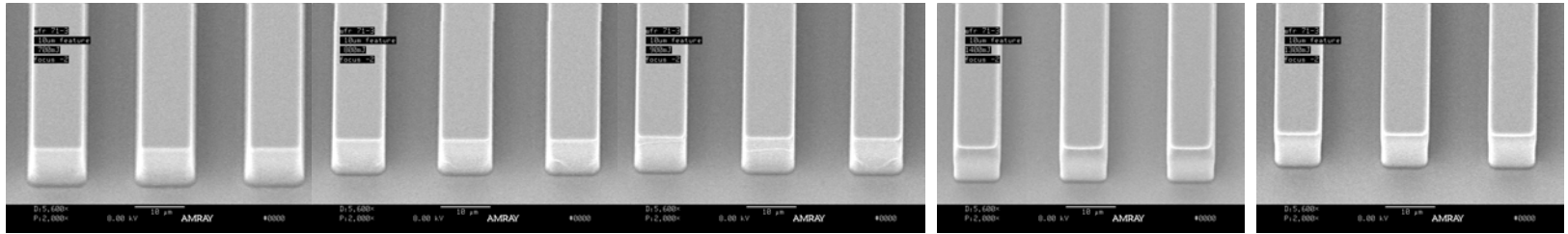


AZ P4620 Lithography performance

900 mJ/cm²

1400 mJ/cm²

1300 mJ/cm²



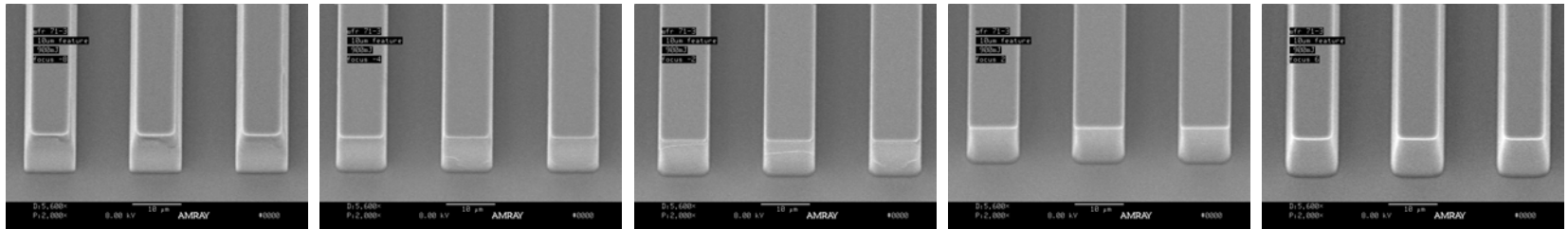
-8.0 µm

-4.0 µm

-2.0 µm

2.0 µm

6.0 µm



Film Thickness: 12 µm

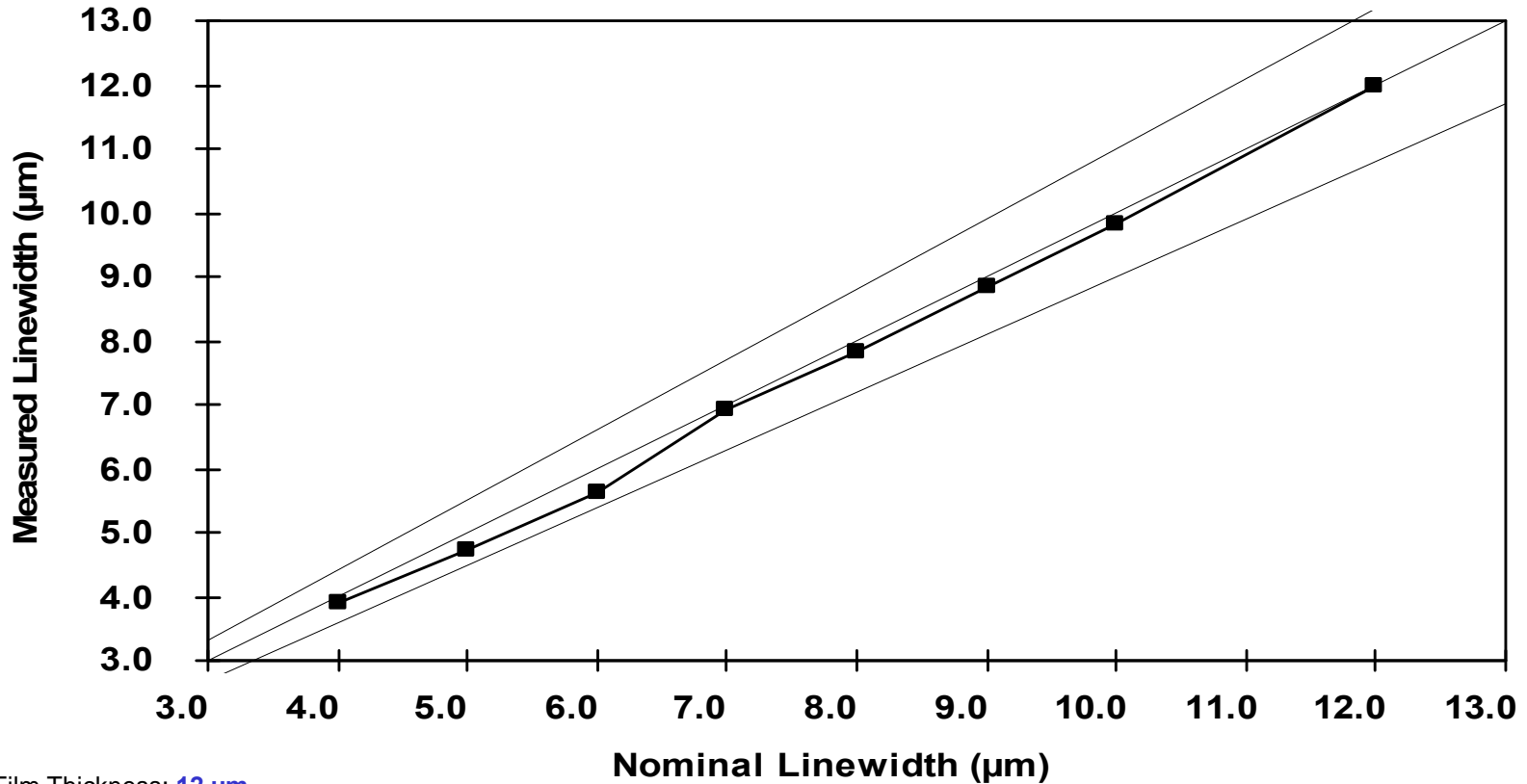
Optitrac coat and Bake

SB: 110 C/ 80 sec

Ultratech 1500 gh line Stepper

AZ 300 MIF, 200 sec continuous spray @ 23 C

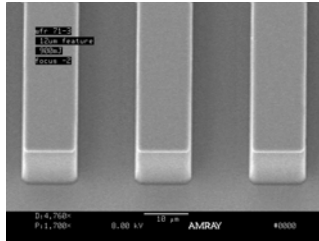
AZ P4620 Lithography performance



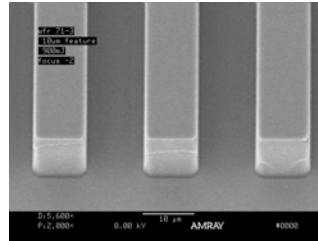
Film Thickness: 12 µm
Optitrac coat and Bake
SB: 110 C / 80 sec
Ultratech 1500 gh line Stepper
AZ 300 MIF, 200 sec continuous spray @ 23 C

AZ P4620 Lithography performance

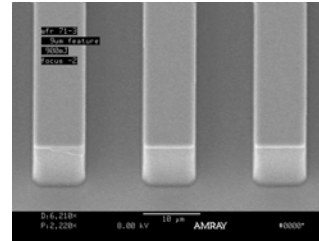
12 μm



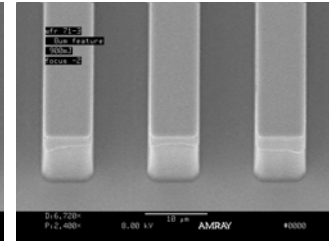
10 μm



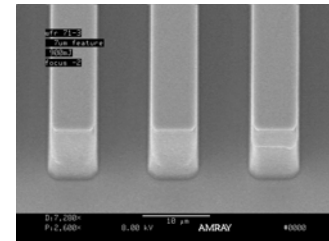
9.0 μm



8.0 μm

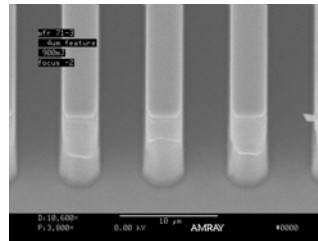


7.0 μm

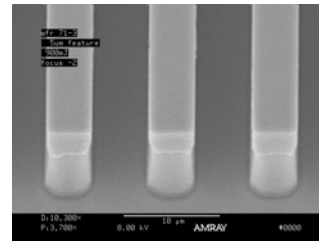


Film Thickness: **12 μm**
 Optitrac coat and Bake
 SB: 110 C / 80 sec
 Ultratech 1500 gh line Stepper
 AZ 300 MIF, 200 sec continuous spray @ 23 C

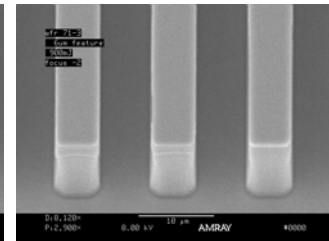
4.0 μm



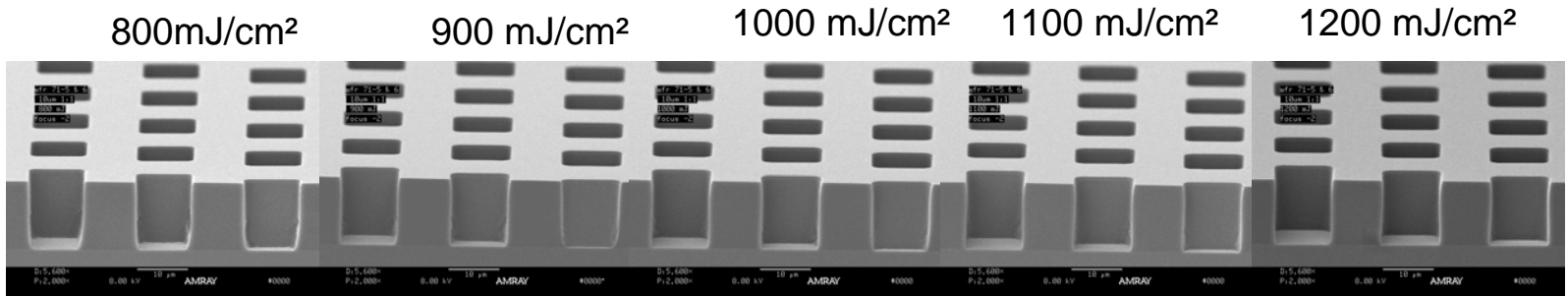
5.0 μm



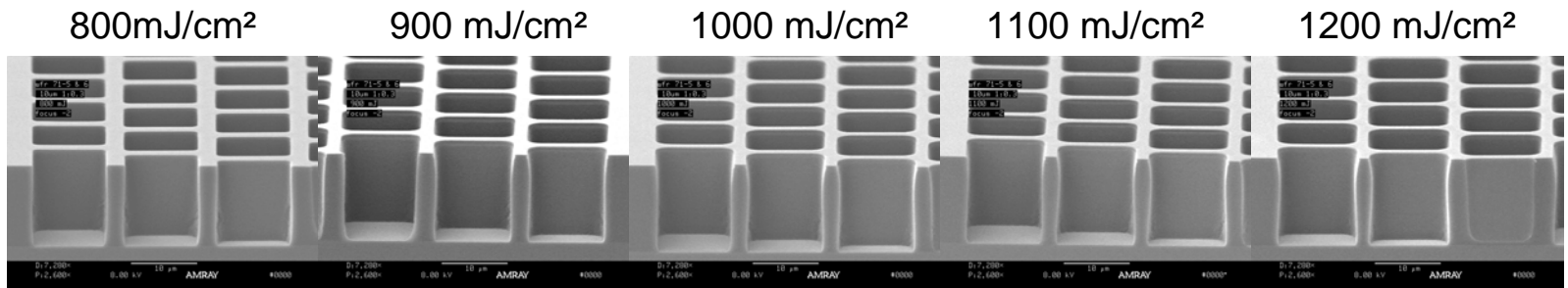
6.0 μm



AZ P4620 Lithography performance



10.0 μm Contact Holes 1:1 Pitch

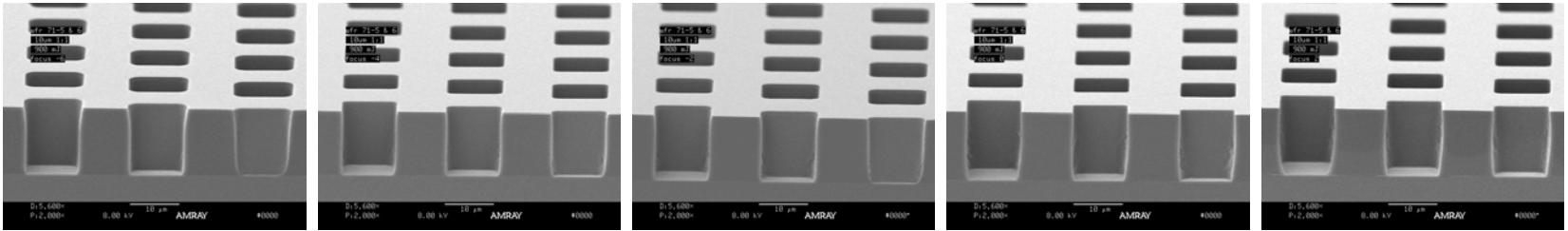


10.0 μm Contact Holes 1:0.3 Pitch

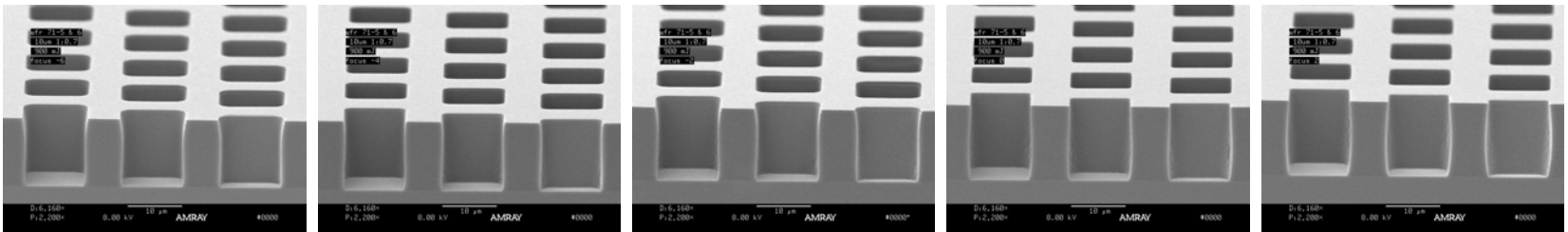
Film Thickness: **12 μm**
 Optitrac coat and Bake
 SB: 110 C / 80 sec
 Ultratech 1500 gh line Stepper
 AZ 300 MIF, 200 sec continuous spray @ 23 C

AZ P4620 Lithography performance

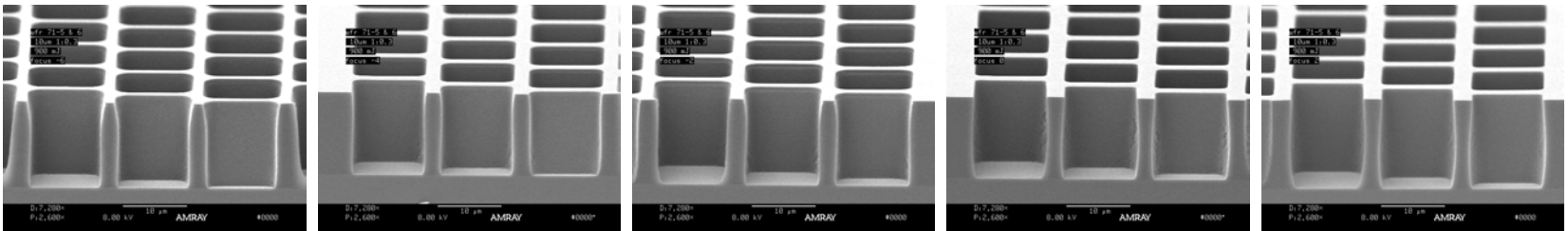
1:1



1:0.7



1:0.3



-6.0 μm

-4.0 μm

-2.0 μm

0.0 μm

2.0 μm

AZ P4620 Lithography performance

Process Conditions:

Optitrac Coat/ Bake

Coat: Static dispense on Silicon

Target Film Thickness: **24 μm**

Softbake: 1st layer 110 C hotplate/ 80 sec. full contact

2nd layer 115 C hotplate/ 180 sec. full contact

Exposure: Ultratech 1500 gh line Stepper

Develop: AZ[®] 400K 1:4, continuous spray for 260 sec. @ 27 C

Analysis:

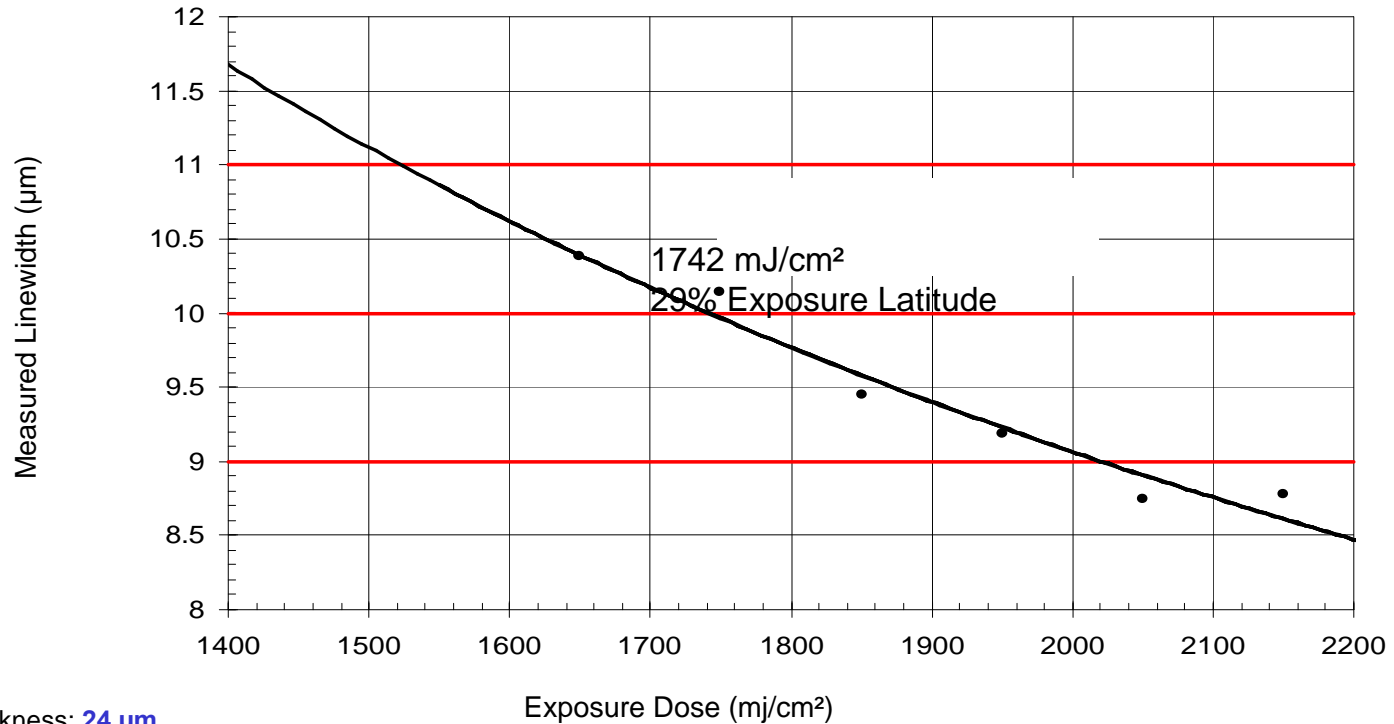
Amray SEM

AZ P4620 Lithography performance

Summary of Results:

	(mm)	DTP 10 mm (mJ/cm ²)	Exposure Latitude 10 mm (%)	DOF 10 mm (mm)	Linearity (mm)
Dense Lines	24	1742	29	16	5.0
Contact Holes	24	1574	39	>8	<10

AZ P4620 Lithography performance



Film Thickness: **24 µm**
Optitrac coat and Bake
SB: 1st layer 110 C / 80 sec
2nd layer 115 C / 180 sec
Ultratech 1500 gh line Stepper
AZ 400K 1:4, 260 sec continuous spray @ 27 C



AZ P4620 Lithography performance

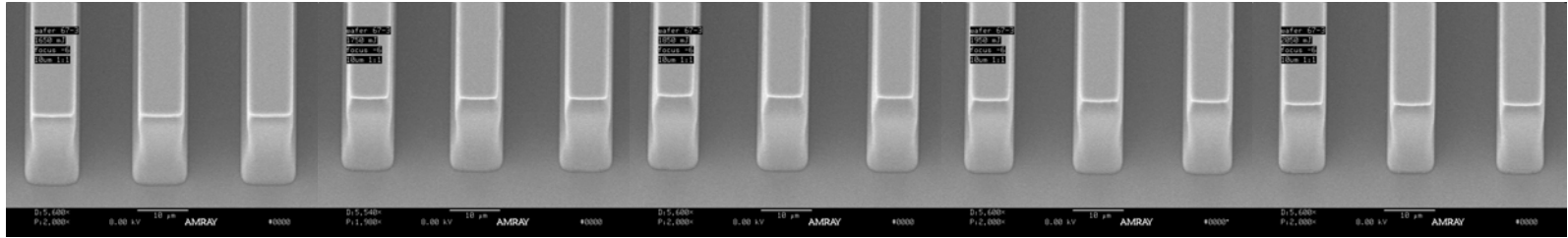
1650 mJ/cm²

1750 mJ/cm²

1850 mJ/cm²

1950 mJ/cm²

2050 mJ/cm²



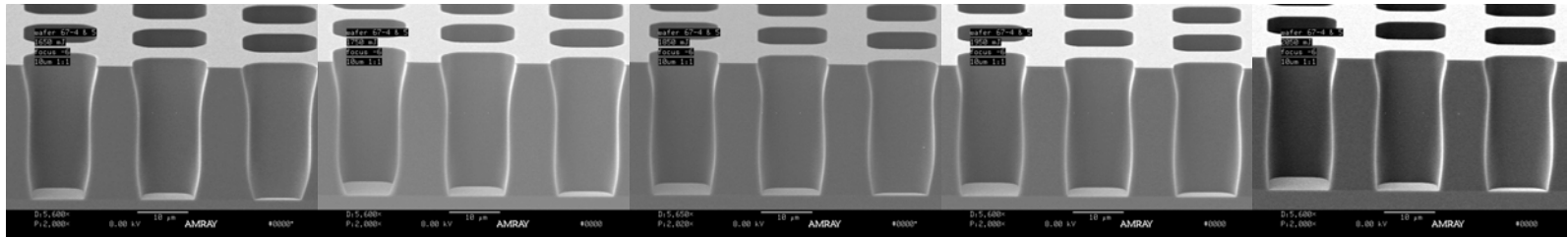
1650 mJ/cm²

1750 mJ/cm²

1850 mJ/cm²

1950 mJ/cm²

2050 mJ/cm²



Film Thickness: 24 µm

Optitrac coat and Bake

SB: 1st layer 110 C / 80 sec

2nd layer 115 C / 180 sec

Ultratech 1500 gh line Stepper

AZ 400K 1:4, 260 sec continuous spray @ 27 C

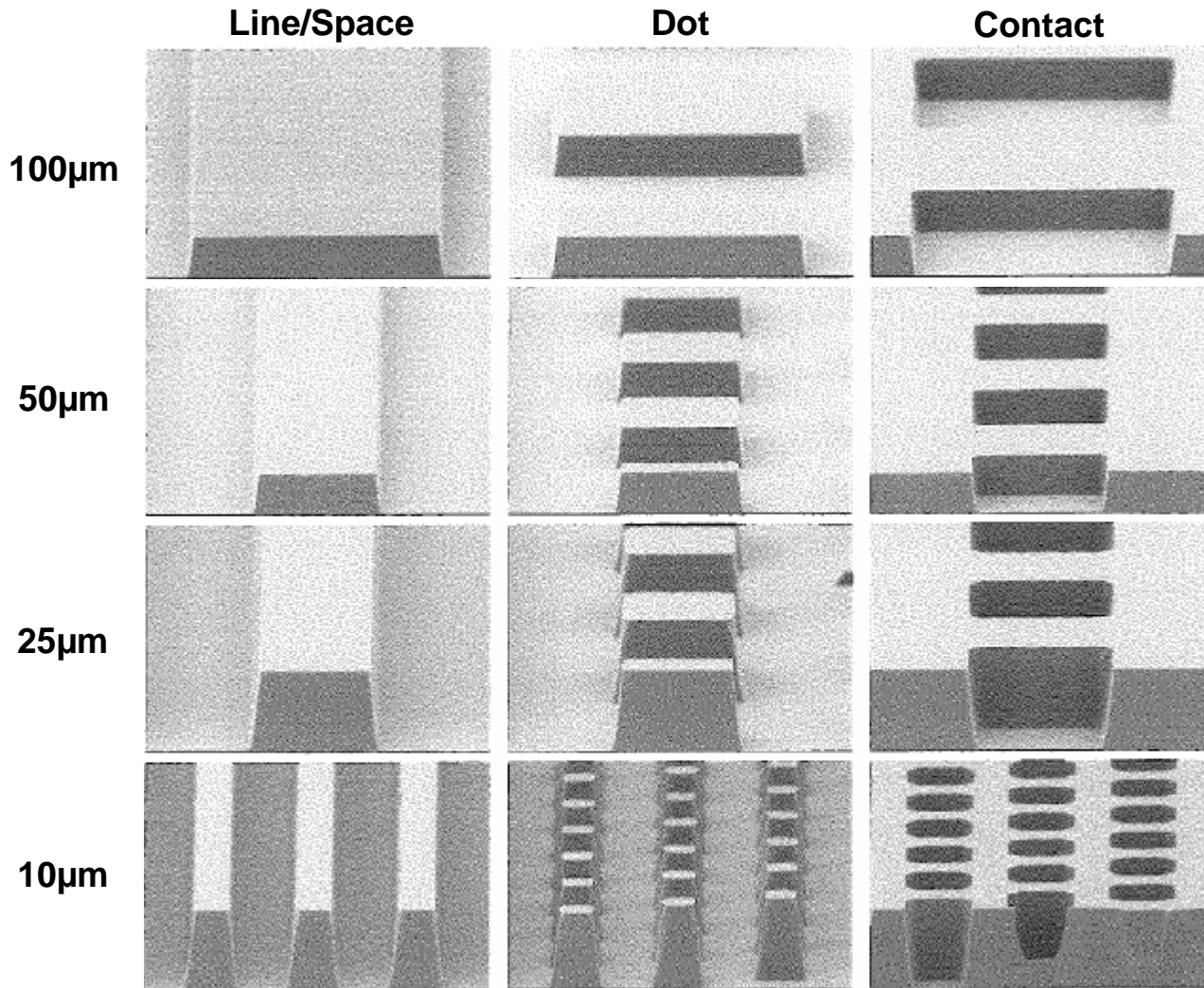
AZ[®] P4620 Lithographic Performance Summary

Process Conditions

Substrate :	Bare-Si
Film-thickness :	17 μ m
Softbake :	120 $^{\circ}$ C / 240 sec. (DHP)
Exposure :	Canon PLA-501F (ghi-line)
Dose :	630 mJ/cm ²
Development :	AZ 400K Developer 1:4, Immersion - 300 sec., 23 $^{\circ}$ C



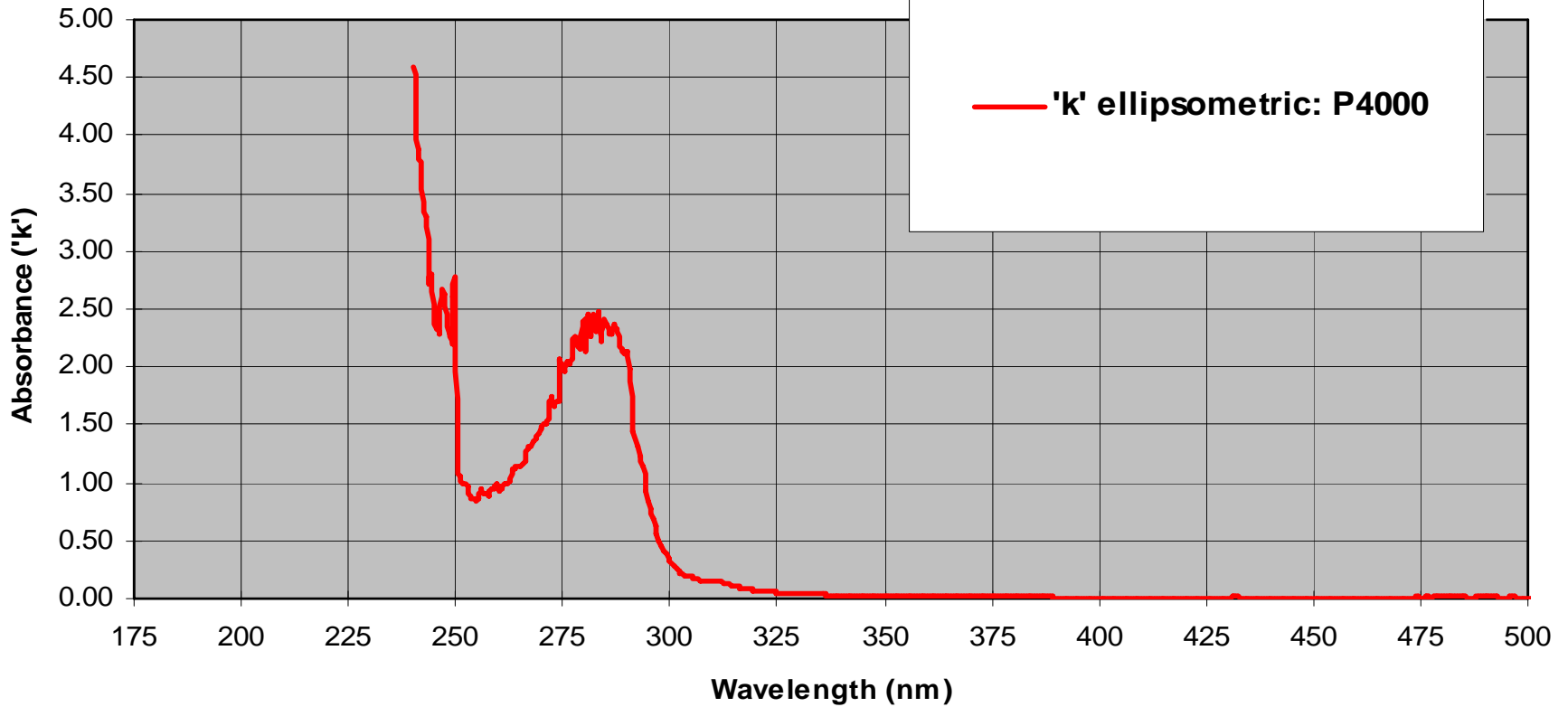
AZ[®] P4620 Lithographic Performance Summary





AZ[®] P4000 Bleached Absorbance Curve

AZ P4000 Series resist(s)
Ellipsometric Absorbance
Normalized to 1/ μm

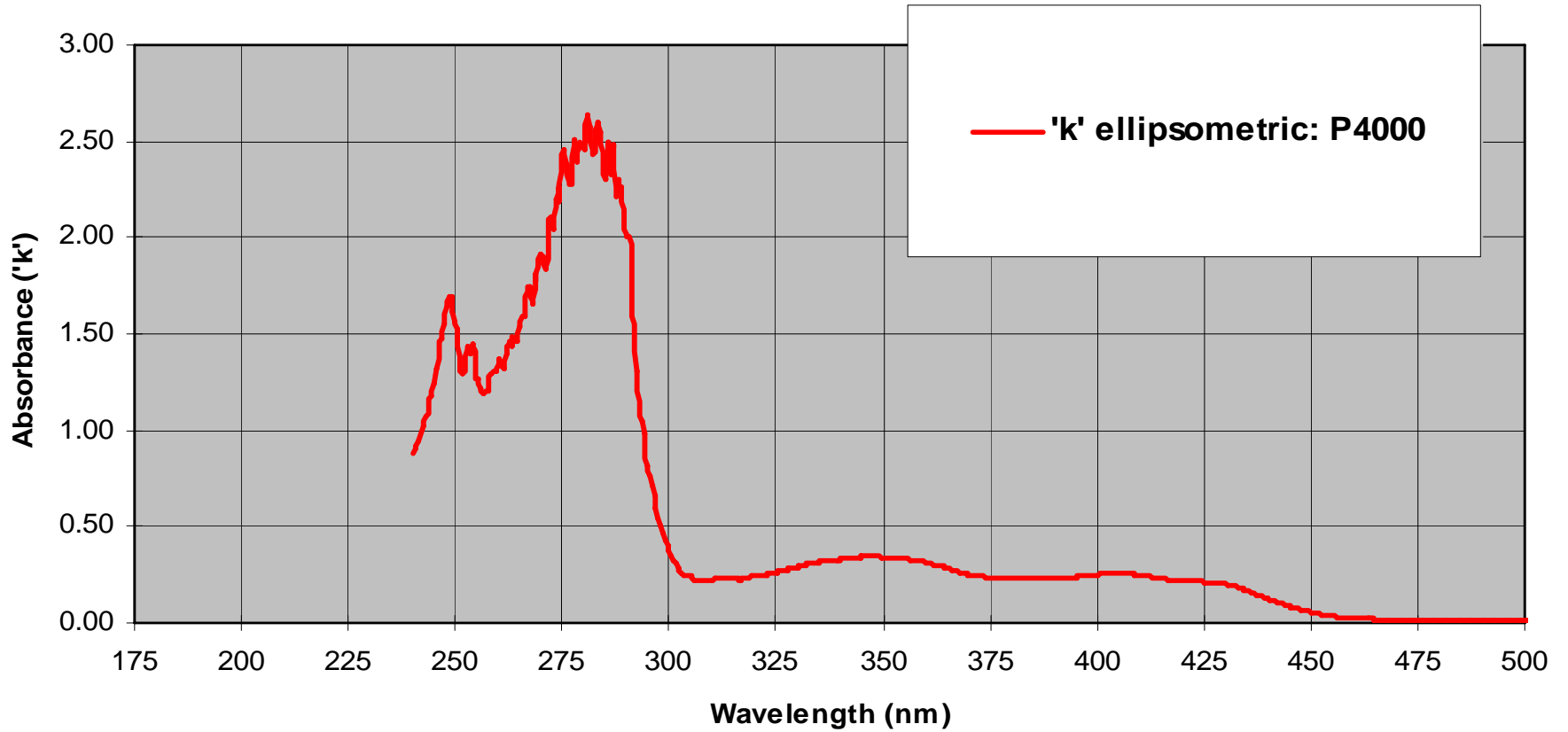


— 'k' ellipsometric: P4000



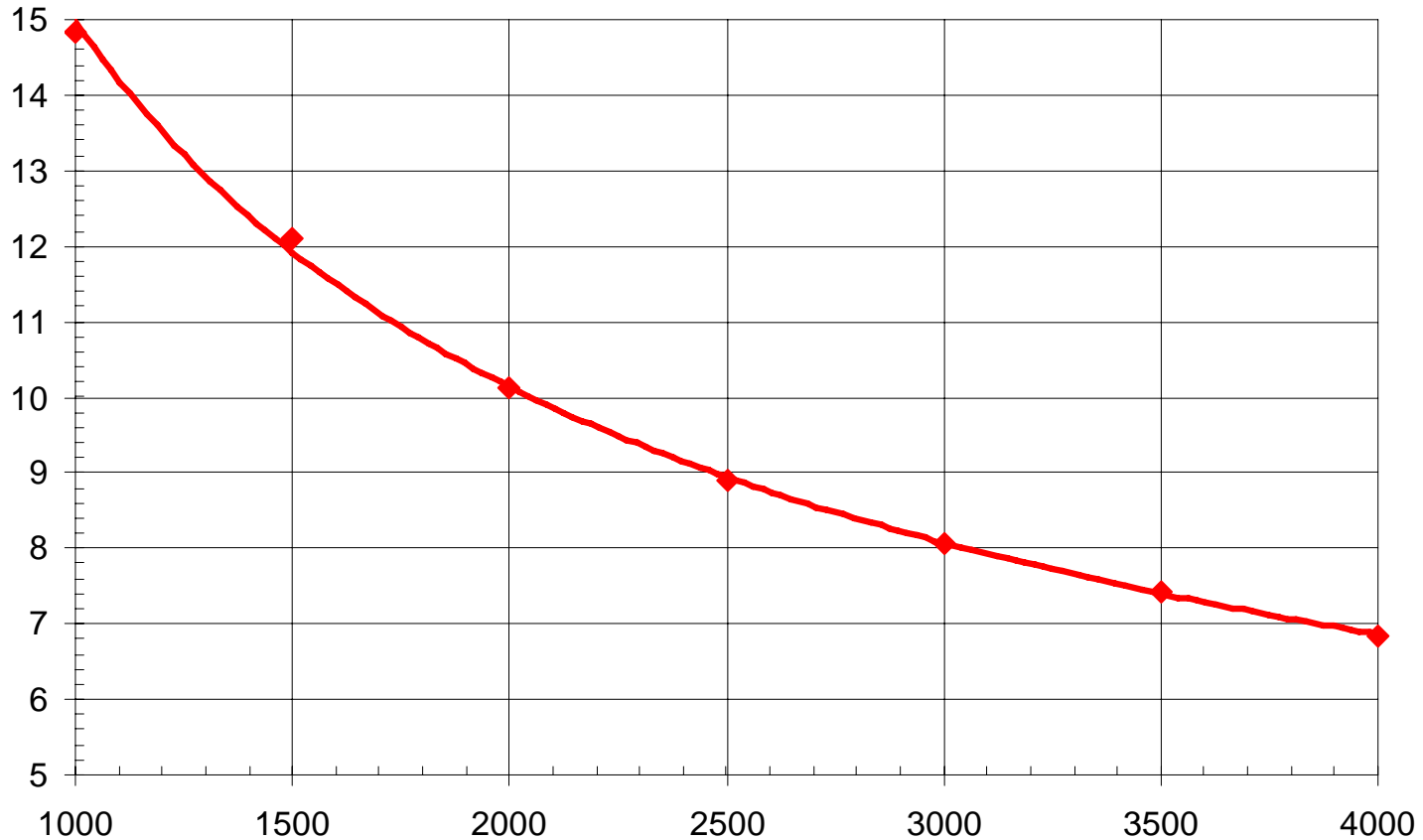
AZ[®] P4000 Unbleached Absorbance Curve

AZ P4000 Series resist(s)
Ellipsometric Absorbance
Normalized to 1/ μm



— 'k' ellipsometric: P4000

AZ[®] P4620 Spin Speed Curve



Substrate: 150 mm Silicon
Softbake: 110°C/ 180 sec hotplate



SEVERAL GRADES AVAILABLE

